

Title (en)  
METHOD OF PRODUCING SEMICONDUCTOR DEVICES

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Application  
**EP 89115504 A 19890823**

Priority  
DE 3828809 A 19880825

Abstract (en)  
[origin: US5096844A] The invention relates to a method in particular for manufacturing bipolar transistors. By applying selective epitaxy methods and by using self-adjusting techniques, the process sequence is shortened and the transistor properties are improved.

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IPC 8 full level  
**H01L 21/20** (2006.01); **H01L 21/285** (2006.01); **H01L 21/331** (2006.01)

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**H01L 21/02381** (2013.01 - EP US); **H01L 21/02392** (2013.01 - EP US); **H01L 21/02395** (2013.01 - EP US); **H01L 21/02461** (2013.01 - EP US); **H01L 21/02463** (2013.01 - EP US); **H01L 21/02543** (2013.01 - EP US); **H01L 21/02546** (2013.01 - EP US); **H01L 21/02639** (2013.01 - EP US); **H01L 21/28525** (2013.01 - EP US); **H01L 29/66242** (2013.01 - EP US); **H01L 29/66287** (2013.01 - EP US); **Y10S 438/969** (2013.01 - EP US)

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